





### 45V NPN SMALL SIGNAL TRANSISTOR IN DFN0806

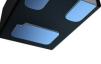
### **Features**

- $BV_{CEO} > 45V$
- I<sub>C</sub> = 100mA high Collector Current
- P<sub>D</sub> = 435mW Power Dissipation
- 0.48mm<sup>2</sup> package footprint, 16 times smaller than SOT23
- 0.4mm height package minimizing off-board profile
- Complementary PNP Type BC857BFA
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

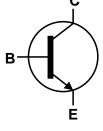
## **Mechanical Data**

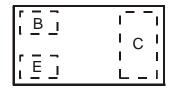
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.0008 grams (approximate)





**Bottom View** 





Device Symbol

Top View Device Schematic

## Ordering Information (Note 4)

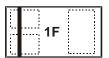
Top View

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BC847BFA-7B	1F	7	8mm	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



Top View Bar Denotes Base and Emitter Side

1F = Product Type Marking Code



## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	45	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Continuous Collector Current	Ic	100	mA
Peak Pulse Collector Current	I <sub>CM</sub>	200	mA

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	435	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	287	°C/W
Thermal Resistance, Junction to Lead (Note 6)	$R_{ heta JL}$	150	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

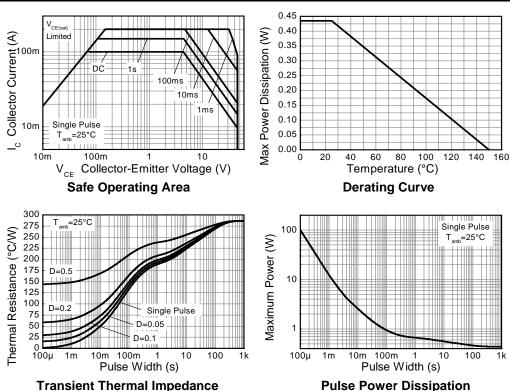
## ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

# Thermal Characteristics and Derating Information





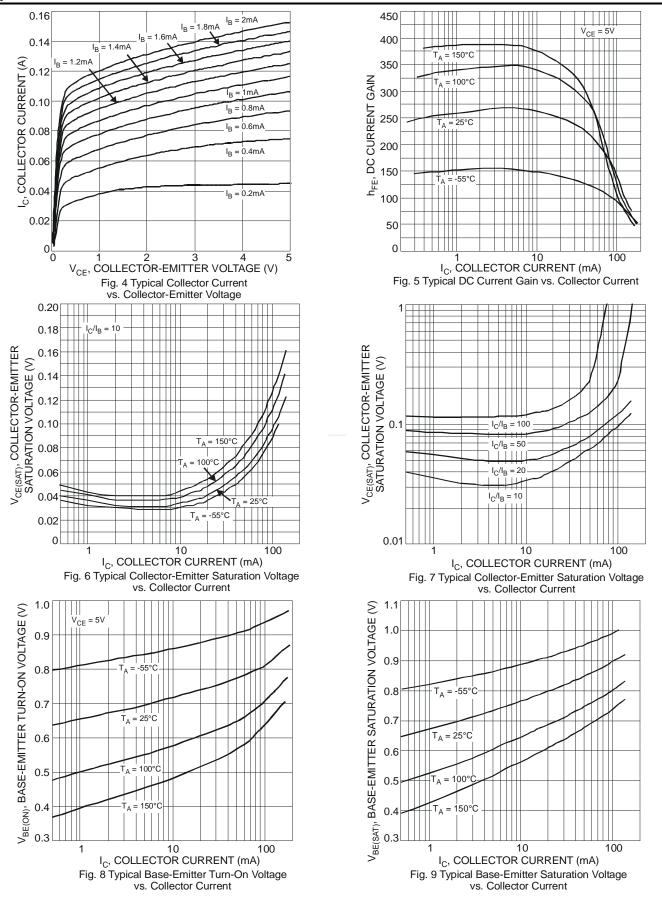
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typical	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	50	150	_	V	$I_C = 50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	50	150	_		$I_C = 50\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 8)	BV <sub>CEO</sub>	45	65	_	V	$I_{C} = 1 \text{mA}, I_{B} = 0$
Collector-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	8.35	_	V	$I_E = 50\mu A, I_C = 0$
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	_	15	nA	V <sub>CB</sub> = 40V
Collector-Emitter Cutoff Current	I <sub>CES</sub>	_	_	15	nA	V <sub>CE</sub> = 40V
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h <sub>FE</sub>	100 200	220 260	— 470	_	$I_C = 10\mu A, V_{CE} = 5.0V$ $I_C = 2.0mA, V_{CE} = 5.0V$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	50 122	125 300	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	760 880	1000 1100	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Voltage	V <sub>BE(on)</sub>	580	650 725	750 800	mV	$I_C = 2.0 \text{mA}, V_{CE} = 5 \text{V}$ $I_C = 10 \text{mA}, V_{CE} = 5 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>	_	1.5	_	pF	$V_{CB} = 10.0V, f = 1.0MHz, I_{E} = 0$
Current Gain-Bandwidth Product	f⊤	100	170	_	MHz	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA, f = 100MHz

Notes: 8. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .



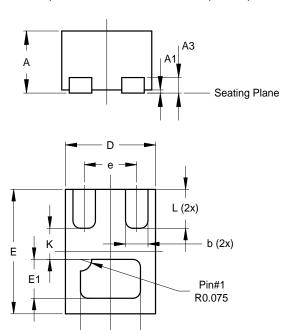
## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

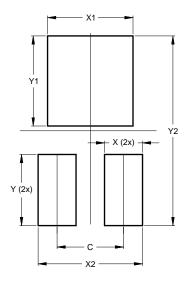


X2-DFN0806-3				
Dim	Min	Max	Тур	
Α	0.375	0.40	0.39	
A1	0	0.05	0.02	
A3	-	-	0.10	
b	0.10	0.20	0.15	
D	0.55	0.65	0.60	
D1	0.35	0.45	0.40	
Е	0.75	0.85	0.80	
E1	0.20	0.30	0.25	
е	-	-	0.35	
K	-	ı	0.20	
L	0.20	0.30	0.25	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

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Dimensions	Value (in mm)		
Dillielisions			
С	0.350		
Х	0.200		
X1	0.450		
X2	0.550		
Υ	0.375		
Y1	0.475		
Y2	1 000		



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